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# **P-Channel NexFET™ Power MOSFET**

Check for Samples: CSD25211W1015

#### **FEATURES**

- Ultra Low On Resistance
- · Ultra Low Qg and Qgd
- Small Footprint 1.0mm x 1.5mm
- Low Profile 0.62mm Height
- · Pb Free
- Gate-Source Voltage Clamp
- Gate ESD Protection 3KV
- RoHS Compliant
- Halogen Free

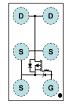
#### **APPLICATIONS**

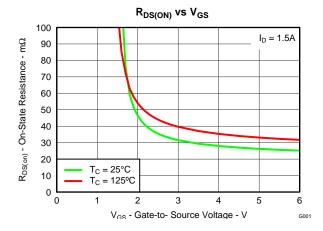
- · Battery Management
- Load Switch
- · Battery Protection

#### DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

**Top View** 





#### PRODUCT SUMMARY

$T_A = 25^{\circ}$	C unless otherwise stated	TYPICAL VA	UNIT			
$V_{DS}$	Drain to Source Voltage	-20	V			
$Q_g$	Gate Charge Total (-4.5V) 3.4					
$Q_{gd}$	Gate Charge Gate to Drain	0.2	nC			
D	Drain to Source On Resistance	$V_{GS} = -2.5V$	36	mΩ		
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = -4.5V	27	mΩ		
V <sub>GS(th)</sub>	Voltage Threshold	ge Threshold -0.8				

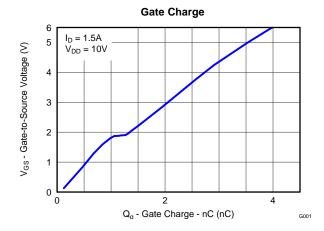
#### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship
CSD25211W1015	1 × 1.5 Wafer Level Package	7-inch reel	3000	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	-20	V
$V_{GS}$	Gate to Source Voltage	-6	V
I <sub>D</sub>	Continuous Drain Current, T <sub>A</sub> = 25°C <sup>(1)</sup>	-3.2	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	-9.5	Α
	Continuous Drain Current, T <sub>A</sub> = 25°C	-0.5	Α
I <sub>G</sub>	Pulsed Drain Current	-7	Α
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	1	W
T <sub>STG</sub>	Storage Temperature Range		
TJ	Operating Junction Temperature Range	–55 to 150	°C

- (1) Typical  $R_{\theta JA} = 119^{\circ}\text{C/W}$  on 1 inch<sup>2</sup> of 2 oz. Cu on 0.06" thick
- (2) Pulse width ≤10µs, duty cycle ≤2%





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**STRUMENTS** 



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

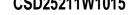
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics					
$BV_{DSS}$	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
BV <sub>GSS</sub>	Gate to Source Voltage	$V_{DS} = 0V, I_{G} = -250\mu A$	-6.1		-7.2	V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -16V			-1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V$ , $V_{GS} = -6V$			-100	nΑ
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.5	-0.8	-1.1	V
D	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -1.5A$		36	44	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -4.5V, I_D = -1.5A$		27	33	mΩ
g <sub>fs</sub>	Transconductance	$V_{DS} = -10V, I_{D} = -1.5A$		12		S
Dynamic	: Characteristics		·		·	
$C_{ISS}$	Input Capacitance			475	570	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		234	281	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			10.5	13.1	pF
$Q_g$	Gate Charge Total (-4.5V)			3.4	4.1	nC
$Q_{gd}$	Gate Charge Gate to Drain	$V_{DS} = -10V, I_D = -1.5A$		0.2		nC
$Q_{gs}$	Gate Charge Gate to Source	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1.5A		1.1		nC
$Q_{g(th)}$	Gate Charge at Vth			0.6		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = -10V$ , $V_{GS} = 0V$		3.8		nC
t <sub>d(on)</sub>	Turn On Delay Time			13.6		ns
t <sub>r</sub>	Rise Time	$V_{DS} = -10V, V_{GS} = -4.5V, I_{D} = -1.5A$		8.8		ns
$t_{d(off)}$	Turn Off Delay Time	$R_G = 4\Omega$		36.9		ns
t <sub>f</sub>	Fall Time			14.2		ns
Diode CI	haracteristics					
$V_{SD}$	Diode Forward Voltage	$I_S = -1.5A, V_{GS} = 0V$		-0.8	-1	V
$Q_{rr}$	Reverse Recovery Charge	$V_{dd}$ = -10V, $I_F$ = -1.5A, di/dt = 200A/µs		6.9		nC
t <sub>rr</sub>	Reverse Recovery Time	$v_{dd} = -10V$ , $v_{f} = -1.5A$ , $v_{f} = 200A/\mu S$		11.6		ns

#### THERMAL CHARACTERISTICS

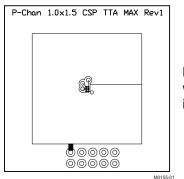
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
В	Thermal Resistance Junction to Ambient (Minimum Cu area)			230	°C/W
R <sub>OJA</sub>	Thermal Resistance Junction to Ambient (1 in <sup>2</sup> Cu area)			149	°C/W

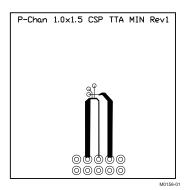




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Max  $R_{\theta JA} = 149^{\circ}C/W$  when mounted on 1 inch2 of 2 oz. Cu.



Max  $R_{\theta JA} = 230^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

#### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

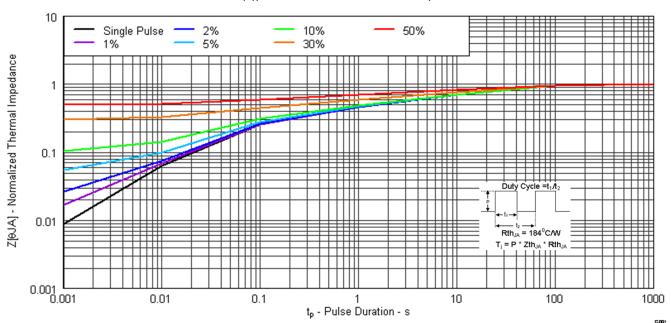


Figure 1. Transient Thermal Impedance

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# **ISTRUMENTS**

# **TYPICAL MOSFET CHARACTERISTICS (continued)**

## $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

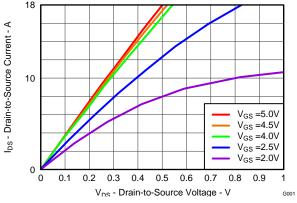


Figure 2. Saturation Characteristics

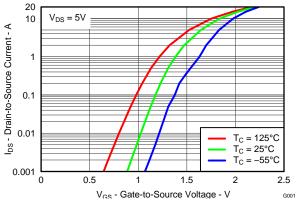
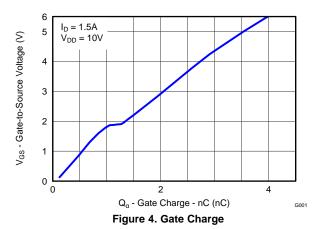


Figure 3. Transfer Characteristics



V<sub>GS(th)</sub> - Threshold Voltage - V 0.9 0.6 0.3

25

 $I_{D} = 250 \mu A$ 

T<sub>C</sub> - Case Temperature - °C Figure 6. Threshold Voltage vs. Temperature

75

125

175

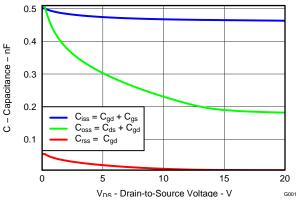


Figure 5. Capacitance

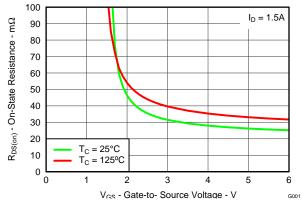


Figure 7. On Resistance vs. Gate Voltage

-25

1.5

1.2

0 **└** -75



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## **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

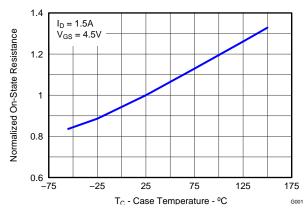


Figure 8. Normalized On Resistance vs. Temperature

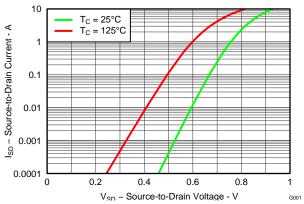


Figure 9. Typical Diode Forward Voltage

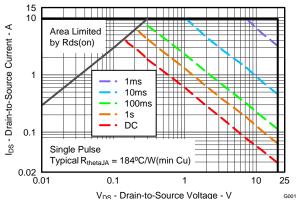


Figure 10. Maximum Safe Operating Area

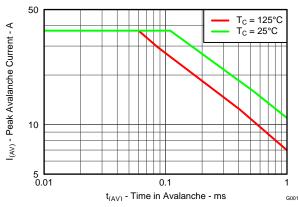


Figure 11. Single Pulse Unclamped Inductive Switching

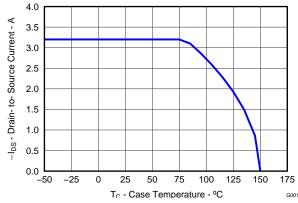
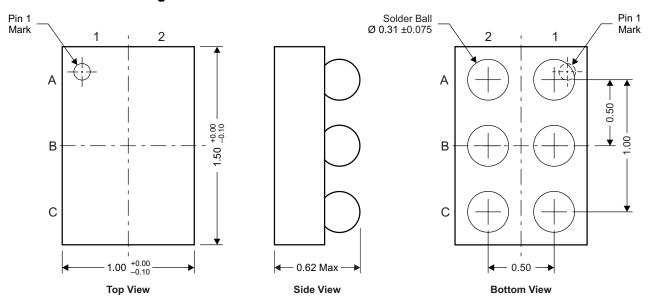


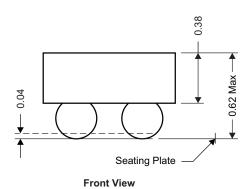
Figure 12. Maximum Drain Current vs. Temperature



#### **MECHANICAL DATA**

# CSD25211W1015 Package Dimensions





M0157-01

NOTE: All dimensions are in mm (unless otherwise specified)

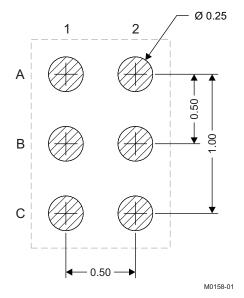
#### **Pinout**

POSITION	DESIGNATION
C1, C2	Drain
A1	Gate
A2, B1, B2	Source



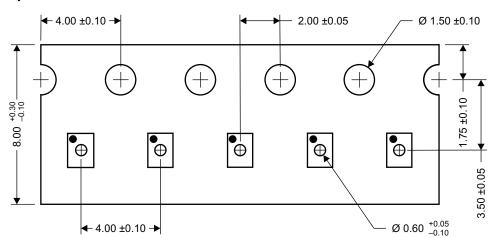
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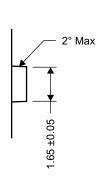
#### **Land Pattern Recommendation**

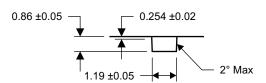


NOTE: All dimensions are in mm (unless otherwise specified)

# **Tape and Reel Information**







M0159-01

NOTE: All dimensions are in mm (unless otherwise specified)



## PACKAGE OPTION ADDENDUM

11-Apr-2013

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	U	Pins	U	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
CSD25211W1015	ACTIVE	DSBGA	YZC	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-55 to 150	25211	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

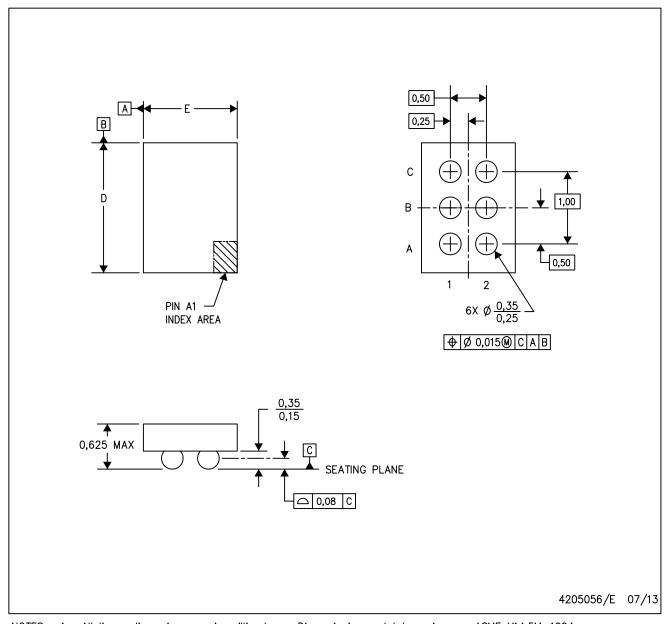
(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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YZC (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



 $NOTES: \quad A. \quad All \ \ linear \ \ dimensions \ \ are \ \ in \ \ millimeters. \quad Dimensioning \ \ and \ \ tolerancing \ \ per \ \ ASME \ \ Y14.5M-1994.$ 

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

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